

Automotive N-Channel 50 V (D-S) 175 °C MOSFET



RoHS
COMPLIANT
HALOGEN
FREE

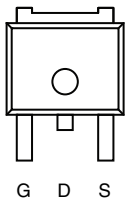
PRODUCT SUMMARY

V_{DS} (V)	50
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.011
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.015
I_D (A)	50
Configuration	Single

FEATURES

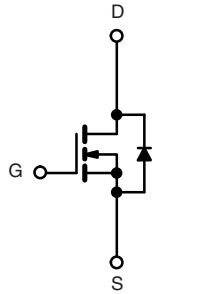
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified^d
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912

TO-252



Top View

Drain Connected to Tab



N-Channel MOSFET

ORDERING INFORMATION

Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50N05-11L-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	50	A
		32	
Continuous Source Current (Diode Conduction) ^a	I_S	50	
Pulsed Drain Current ^b	I_{DM}	200	
Single Pulse Avalanche Energy	I_{AS}	45	
Single Pulse Avalanche Current	E_{AS}	101	mJ
Maximum Power Dissipation ^b	P_D	75	W
		25	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	60	°C/W
Junction-to-Case (Drain)	R_{thJC}	2.0	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		50	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 50 V	-	-	1.0	μA
		V _{GS} = 0 V	V _{DS} = 50 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 50 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 45 A	-	0.009	0.011	Ω
		V _{GS} = 10 V	I _D = 45 A, T _J = 125 °C	-	-	0.020	
		V _{GS} = 10 V	I _D = 45 A, T _J = 175 °C	-	-	0.024	
		V _{GS} = 4.5 V	I _D = 20 A	-	-	0.015	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	58	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	1685	2106	pF
Output Capacitance	C _{oss}			-	345	430	
Reverse Transfer Capacitance	C _{rss}			-	144	180	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 25 V, I _D = 43 A	-	34.6	52	nC
Gate-Source Charge ^c	Q _{gs}			-	5.5	9	
Gate-Drain Charge ^c	Q _{gd}			-	9.1	14	
Gate Resistance	R _g	f = 1 MHz		1.3	2.6	3.9	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 25 V, R _L = 0.6 Ω I _D ≅ 43 A, V _{GEN} = 10 V, R _g = 1 Ω		-	8.5	13	ns
Rise Time ^c	t _r			-	11.5	18	
Turn-Off Delay Time ^c	t _{d(off)}			-	22.5	34	
Fall Time ^c	t _f			-	7.5	12	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	200	A
Forward Voltage	V _{SD}	I _F = 45 A, V _{GS} = 0 V		-	0.95	1.5	V

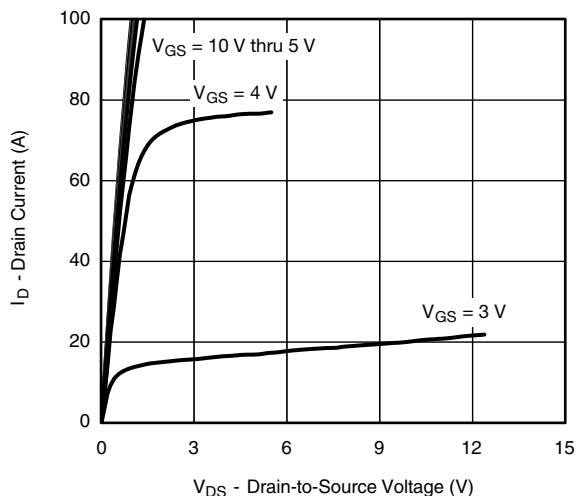
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

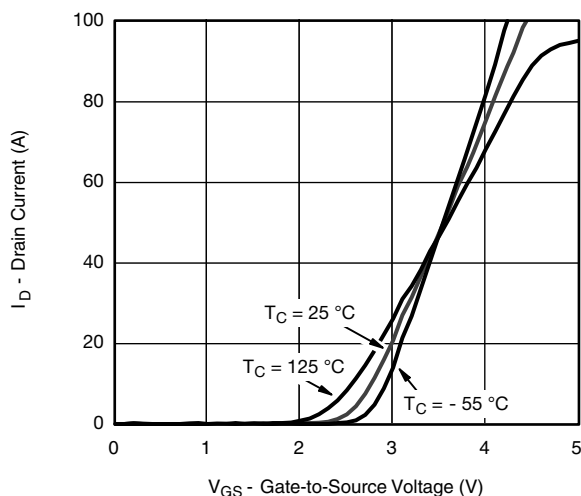
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



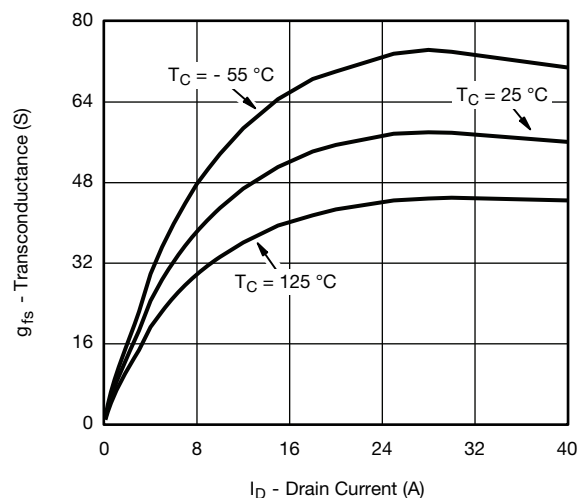
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



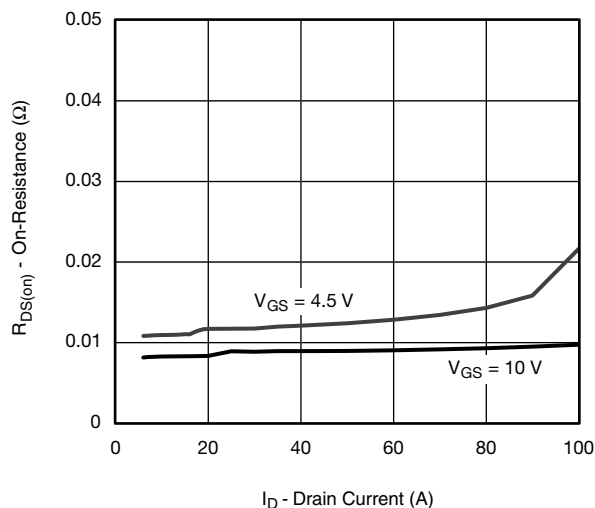
Output Characteristics



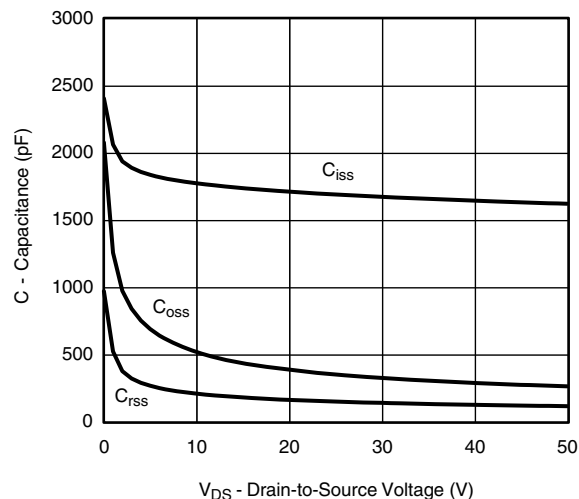
Transfer Characteristics



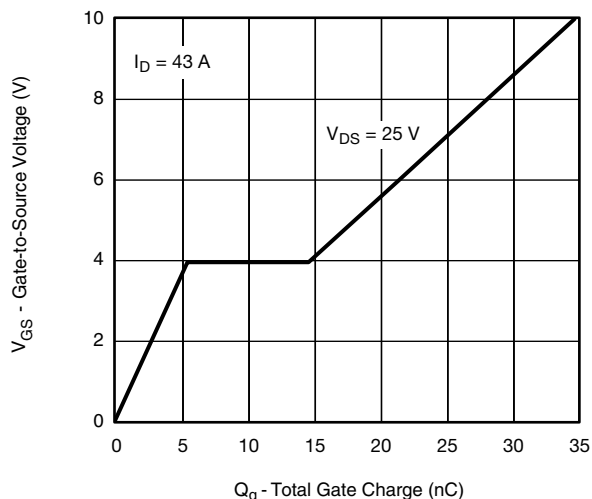
Transconductance



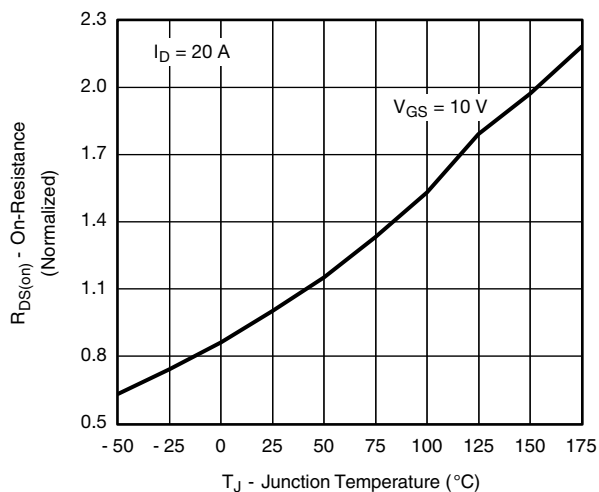
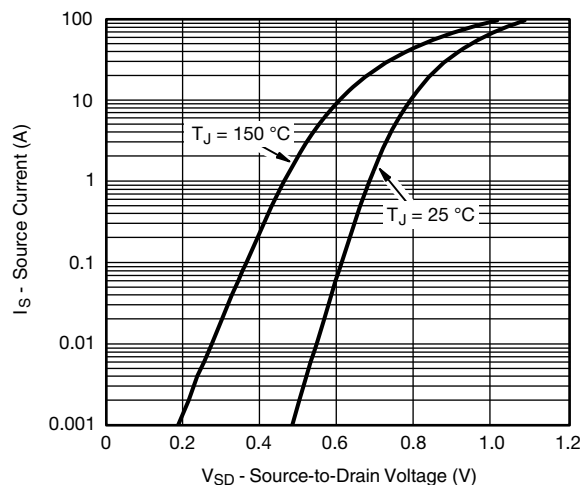
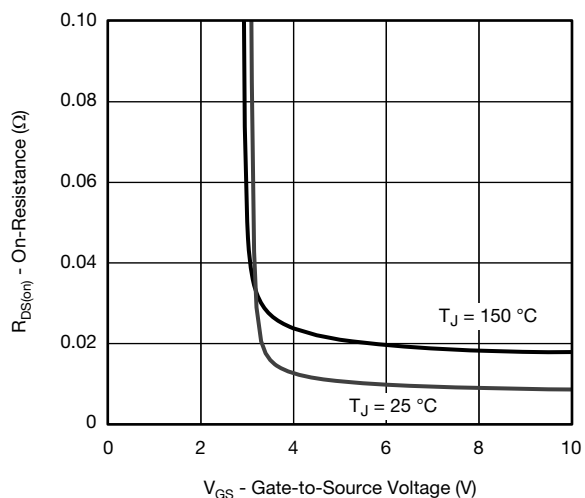
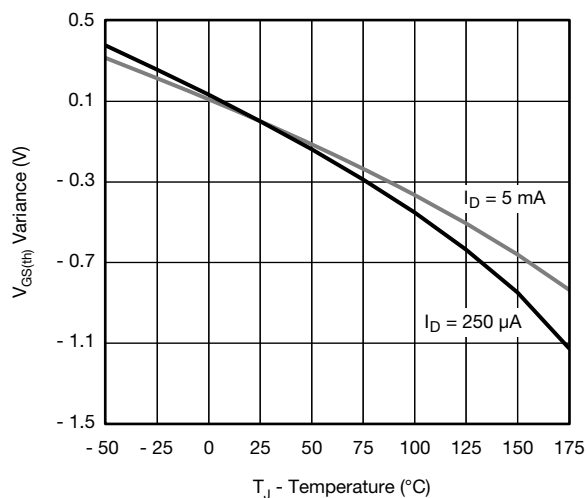
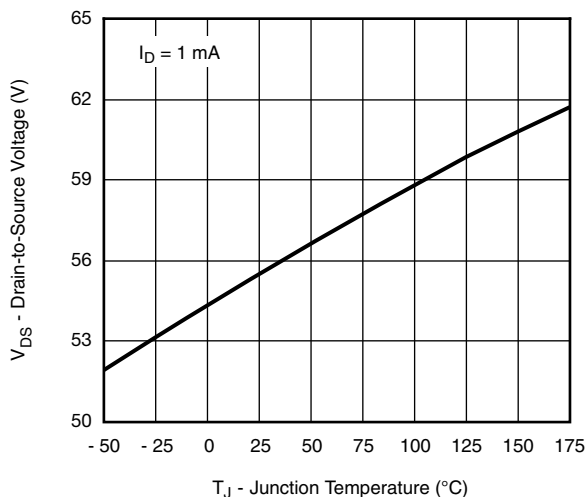
On-Resistance vs. Drain Current



Capacitance

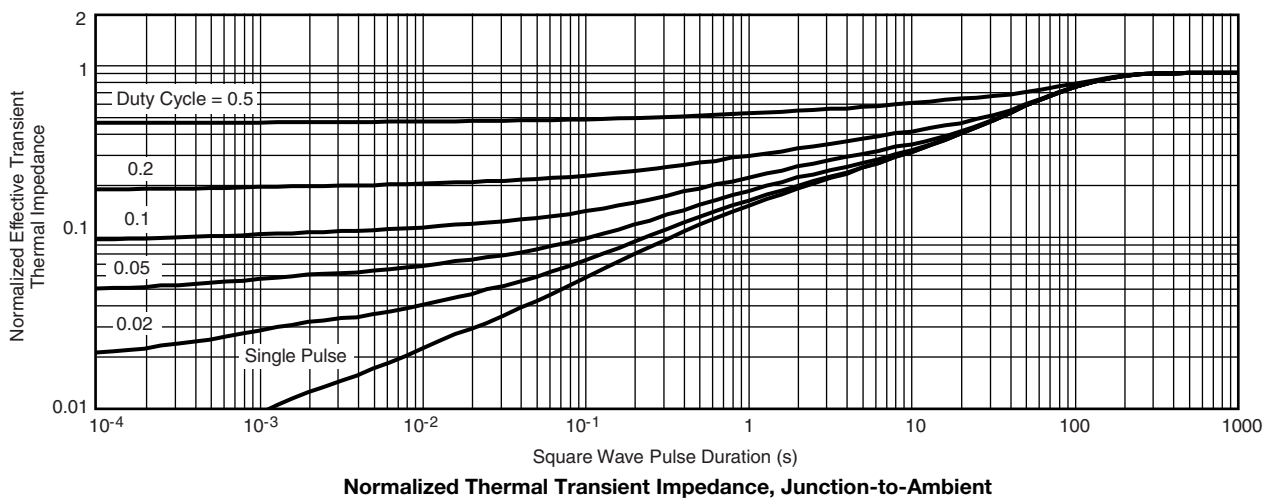
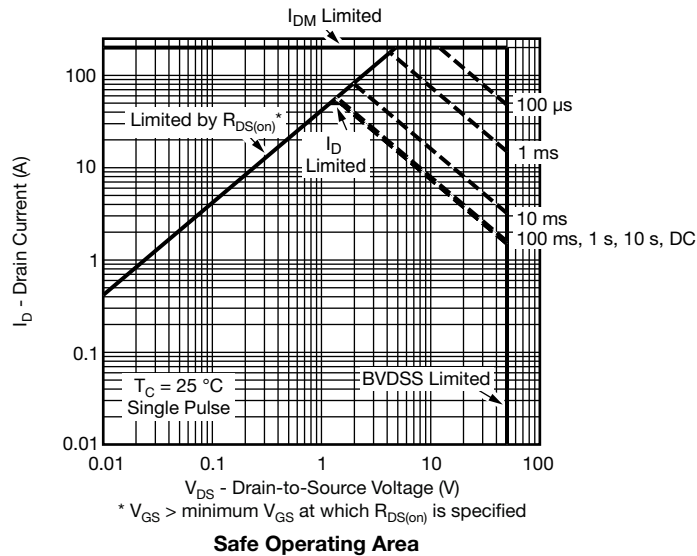


Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

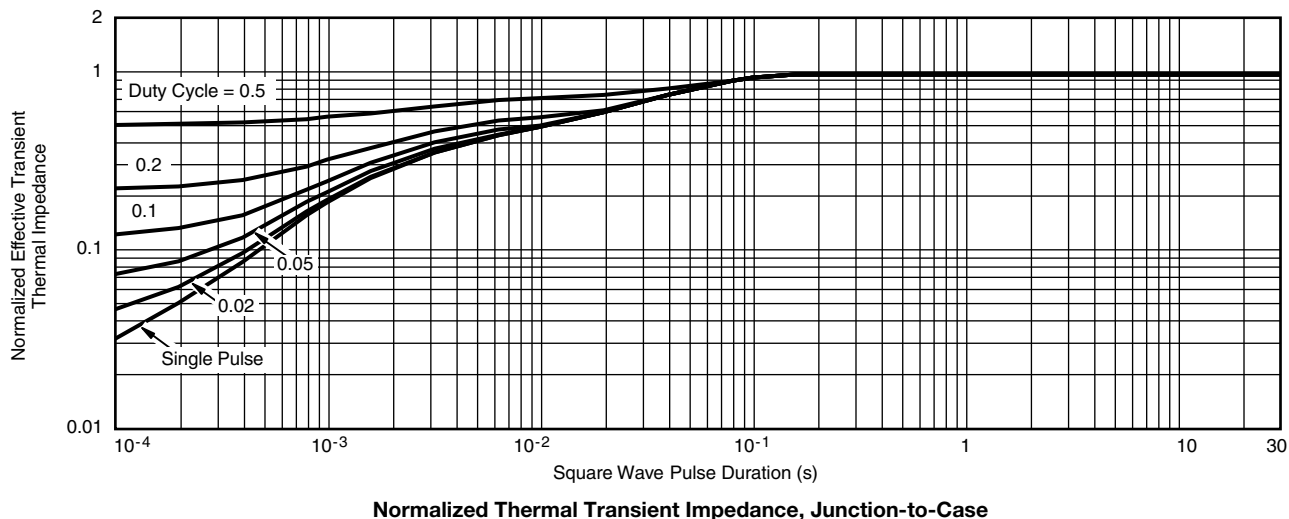


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-252AA Case Outline



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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